

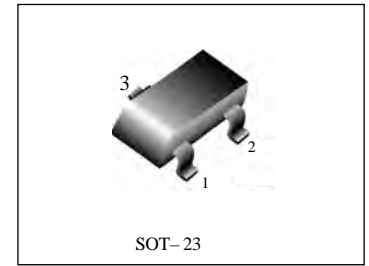
General Purpose Transistors

NPN Silicon

- We declare that the material of product compliance with RoHS requirements.

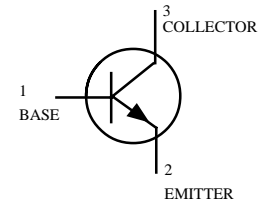
ORDERING INFORMATION

Device	Marking	Shipping
FTC3904H	G1F	3000 Tape & Reel



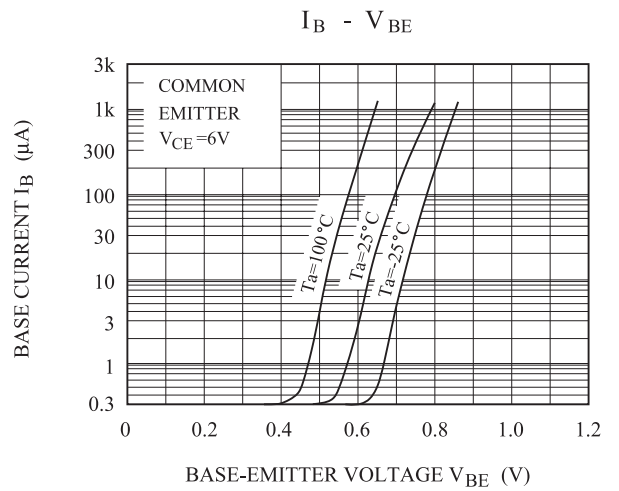
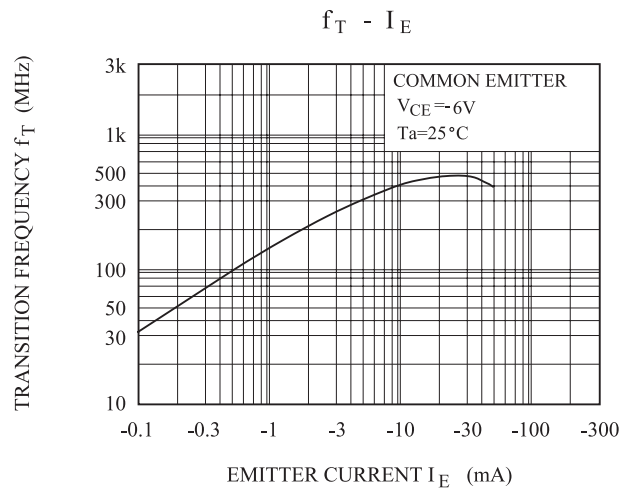
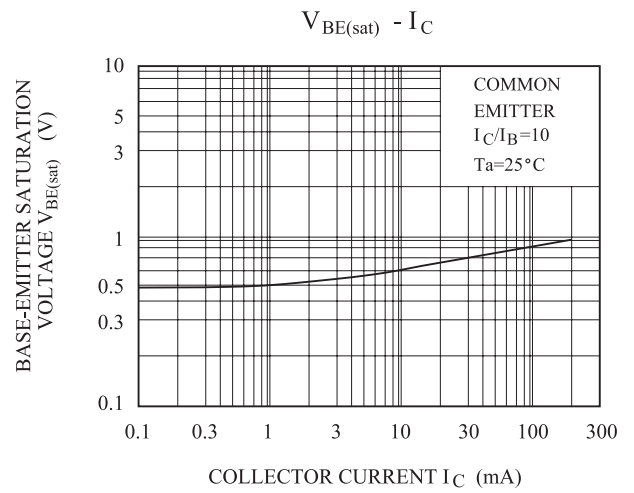
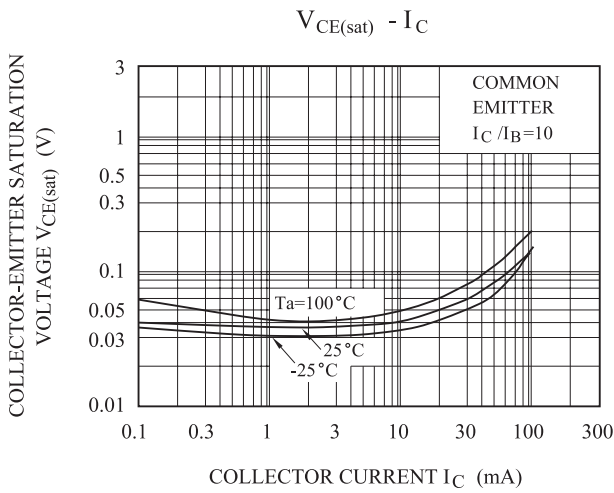
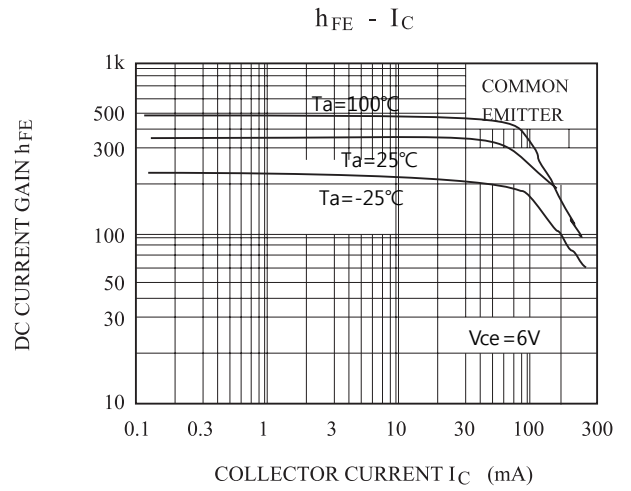
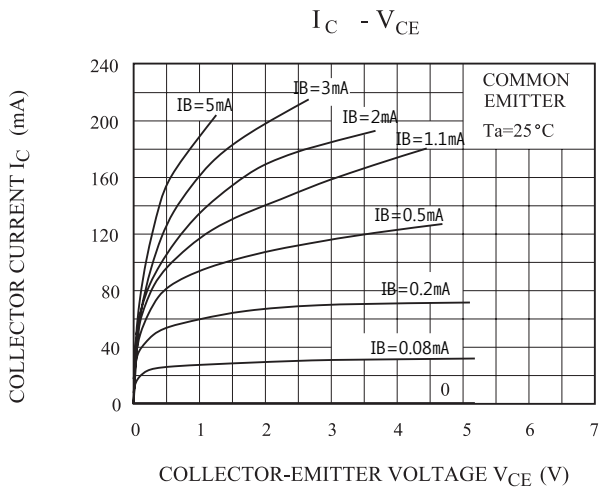
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	V
Collector-Base Voltage	V_{CBO}	60	V
Emitter-Base Voltage	V_{EBO}	7.0	V
Collector Current — Continuous	I_C	150	mAdc
Collector power dissipation	P_C	0.2	W
Junction temperature	T_j	150	C
Storage temperature	T_{stg}	-55 ~ +150	C



ELECTRICAL CHARACTERISTICS ($T_A = 25$ C unless otherwise noted.)

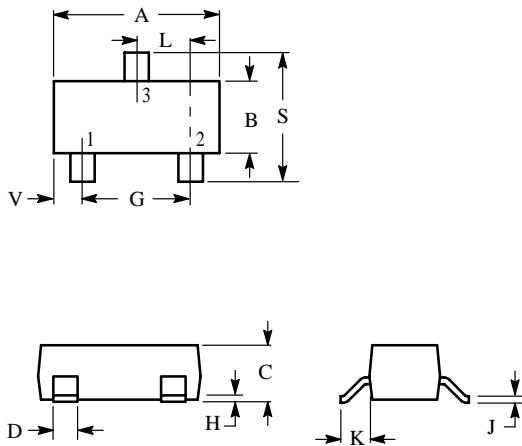
Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage ($I_C = 1$ mA)	$V_{(BR)CEO}$	50	-	-	V
Emitter-Base Breakdown Voltage ($I_E = 50$ μ A)	$V_{(BR)EBO}$	7	-	-	V
Collector-Base Breakdown Voltage ($I_C = 50$ μ A)	$V_{(BR)CBO}$	60	-	-	V
Collector Cutoff Current ($V_{CB} = 60$ V)	I_{CBO}	-	-	0.1	μ A
Emitter cutoff current ($V_{EB} = 7$ V)	I_{EBO}	-	-	0.1	μ A
Collector-emitter saturation voltage ($I_C / I_B = 50$ mA / 5 mA)	$V_{CE(sat)}$	-	-	0.4	V
DC current transfer ratio h FE ($V_{CE} = 6$ V, $I_C = 1$ mA)	h_{FE}	270	-	560	-
Transition frequency ($V_{CE} = 12$ V, $I_E = -2$ mA, $f = 30$ MHz)	f_T	-	180	-	MHz
Output capacitance ($V_{CB} = 12$ V, $I_E = 0$ A, $f = 1$ MHz)	C_{ob}	-	2.0	3.5	pF



SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

